

YJ Planar Fast Recovery Diode Die Specification

600V 8A, Fast recovery diode die based on silicon planar process
Part No.: FRD08A600AS-290A

Main Products Characterstics

Maximum Ratings			Static Electrical Characteristics (Ta = 25°C)		
Parameter	Symbol	Rating	Parameter	Symbol	Value
Repetitive peak reverse voltage	V_{RRM}	600V	Reverse breakdown voltage		630V
Average forward current		8A	$I_R = 50\mu A$		680V
(tp = 8.3 ms, halfwave, 1 cycle)	I_{FSM}	80A	$I_F \leq 2\%$		1.6V
Storage temperature range	T_{stg}	-40 to +150 °C	Reverse Recovery Time	T_{rr}	28ns
			$I_F=0.5A, I_R=1A, I_{rr}=0.25A$		
Maximum operating junction temperature	T_j	150 °C	Maximum reverse current	$V_R = V_{RRM} \leq 2\%$	2uA

Device Schematics and Outline Drawing

	Die Thickness
	Die Size *
	Top Metal Pad
	Active Area
	Top Metal
	Back Metal
	Note: 1 *: Cutting street width is around 40um

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.	Recommended Storage Environment:
does not guarantee device performance after assembly.	Store in original container, in dessicated nitrogen, with no contamination.
All operating parameters must be validated for each customer application by customer's technical experts.	Shelf life for parts stored in above condition is 2 years.
Data sheet information is subjected to change without notice.	If the storage is done in normal atmosphere shelf life is reduced to 6 months.

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